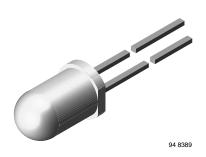
**GREEN** 

<u>(5-2008)</u>\*\*



# Vishay Semiconductors

# High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero



## DESCRIPTION

TSHG6210 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

#### **FEATURES**

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

Peak wavelength: λ<sub>p</sub> = 850 nm

· High reliability

· High radiant power

• High radiant intensity

• Angle of half intensity:  $\phi = \pm 10^{\circ}$ 

· Low forward voltage

· Suitable for high pulse current operation

• High modulation bandwidth: f<sub>c</sub> = 18 MHz

· Good spectral matching with CMOS cameras

 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### **APPLICATIONS**

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- Smoke-automatic fire detectors

| PRODUCT SUMMARY |                        |         |                      |    |  |
|-----------------|------------------------|---------|----------------------|----|--|
| COMPONENT       | I <sub>e</sub> (mW/sr) | φ (deg) | $φ$ (deg) $λ_p$ (nm) |    |  |
| TSHG6210        | 230                    | ± 10    | 850                  | 20 |  |

#### Note

• Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION |           |                              |              |  |  |
|----------------------|-----------|------------------------------|--------------|--|--|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |  |  |
| TSHG6210             | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾         |  |  |

#### Note

· MOQ: minimum order quantity

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified) |  |                   |               |      |  |
|--|--|-------------------|---------------|------|--|
| PARAMETER  | TEST CONDITION                         | SYMBOL            | VALUE         | UNIT |  |
| Reverse voltage  |  | $V_R$             | 5             | V    |  |
| Forward current  |  | I <sub>F</sub>    | 100           | mA   |  |
| Peak forward current   | $t_p/T = 0.5$ , $t_p = 100 \mu s$      | I <sub>FM</sub>   | 200           | mA   |  |
| Surge forward current  | t <sub>p</sub> = 100 μs                | I <sub>FSM</sub>  | 1             | Α    |  |
| Power dissipation  |  | P <sub>V</sub>    | 180           | mW   |  |
| Junction temperature   |  | T <sub>j</sub>    | 100           | °C   |  |
| Operating temperature range  |  | T <sub>amb</sub>  | - 40 to + 85  | °C   |  |
| Storage temperature range  |  | T <sub>stg</sub>  | - 40 to + 100 | °C   |  |
| Soldering temperature  | t ≤ 5 s, 2 mm from case                | T <sub>sd</sub>   | 260           | °C   |  |
| Thermal resistance junction/ambient  | J-STD-051, leads 7 mm, soldered on PCB | R <sub>thJA</sub> | 230           | K/W  |  |





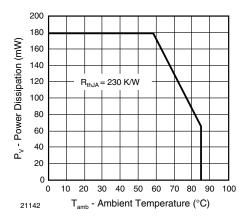


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

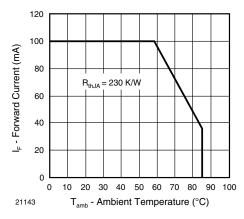


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| PARAMETER                                 | CS (T <sub>amb</sub> = 25 °C, unless other TEST CONDITION | SYMBOL           | MIN.     | TYP.   | MAX. | UNIT  |
|---|---|------------------|----------|--------|------|-------|
| TAHAMETER                                 |   |                  | IVIII V. |        |      | _     |
| Forward voltage                           | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$               | V <sub>F</sub>   |          | 1.5    | 1.8  | V     |
|   | $I_F = 1 \text{ A}, t_p = 100 \mu s$                      | $V_{F}$          |          | 2.3    |      | V     |
| Temperature coefficient of V <sub>F</sub> | I <sub>F</sub> = 1 mA                                     | TK <sub>VF</sub> |          | - 1.8  |      | mV/K  |
| Reverse current                           | V <sub>R</sub> = 5 V                                      | I <sub>R</sub>   |          |        | 10   | μA    |
| Junction capacitance                      | $V_R = 0 V, f = 1 MHz, E = 0$                             | C <sub>j</sub>   |          | 125    |      | pF    |
| Radiant intensity                         | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$               | l <sub>e</sub>   | 140      | 230    | 420  | mW/sr |
|   | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs             | I <sub>e</sub>   |          | 2300   |      | mW/sr |
| Radiant power                             | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$               | фe               |          | 55     |      | mW    |
| Temperature coefficient of φ <sub>e</sub> | I <sub>F</sub> = 100 mA                                   | TKφ <sub>e</sub> |          | - 0.35 |      | %/K   |
| Angle of half intensity                   |   | φ                |          | ± 10   |      | deg   |
| Peak wavelength                           | I <sub>F</sub> = 100 mA                                   | λρ               | 820      | 850    | 880  | nm    |
| Spectral bandwidth                        | I <sub>F</sub> = 100 mA                                   | Δλ               |          | 40     |      | nm    |
| Temperature coefficient of $\lambda_p$    | I <sub>F</sub> = 100 mA                                   | TKλ <sub>p</sub> |          | 0.25   |      | nm/K  |
| Rise time                                 | I <sub>F</sub> = 100 mA                                   | t <sub>r</sub>   |          | 20     |      | ns    |
| Fall time                                 | I <sub>F</sub> = 100 mA                                   | t <sub>f</sub>   |          | 13     |      | ns    |
| Cut-off frequency                         | I <sub>DC</sub> = 70 mA, I <sub>AC</sub> = 30 mA pp       | f <sub>c</sub>   |          | 18     |      | MHz   |
| Virtual source diameter                   |   | d                |          | 3.7    |      | mm    |



#### BASIC CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

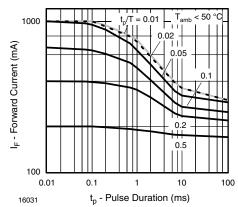


Fig. 3 - Pulse Forward Current vs. Pulse Duration

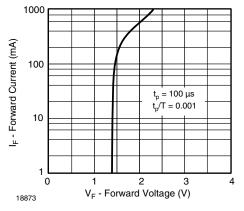


Fig. 4 - Forward Current vs. Forward Voltage

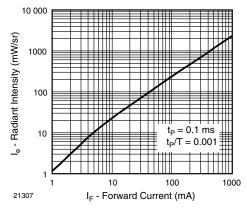


Fig. 5 - Radiant Intensity vs. Forward Current

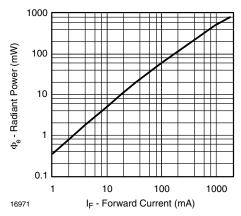


Fig. 6 - Radiant Power vs. Forward Current

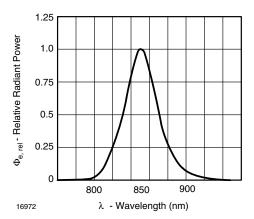


Fig. 7 - Relative Radiant Power vs. Wavelength

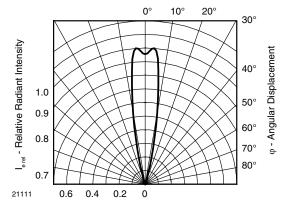
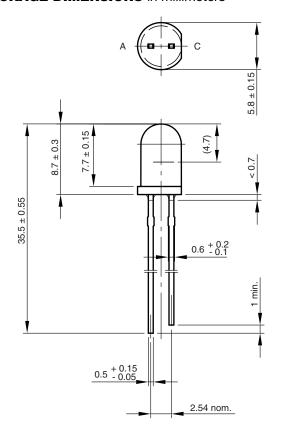
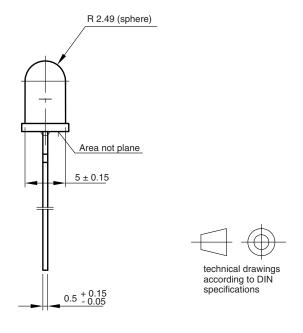


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

# Vishay Semiconductors

#### **PACKAGE DIMENSIONS** in millimeters





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